Maximum Ratings, NPN Transistor Element (Q1) (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	40	V
Emitter-Base Voltage		V_{EBO}	6.0	V
Collector Current - Continuous	(Note 5)	I_C	600	mA

Maximum Ratings, Zener Element (Z1) (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Forward Voltage	@ I_F = 10mA	V_F	0.9	V

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	300	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Note: 5. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com/package-outlines.html.

Electrical Characteristics, NPN Transistor Element (Q1) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	I_C = 100µA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	V	I_E = 100µA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
Base Cutoff Current	I_{BL}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	20 40 80 100 40	— — — 300 —	—	I_C = 100µA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 150mA, V_{CE} = 1.0V I_C = 500mA, V_{CE} = 2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.40 0.75	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75 —	0.95 1.2	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA

Electrical Characteristics, Zener Element (Z1) (@T_A = +25°C, unless otherwise specified.)

Zener Voltage Range (Note 6)				Maximum Zener Impedance		Maximum Reverse Leakage Current (Note 6)	
V_Z @ I_{ZT}			I_{ZT}	Z_{ZT} @ I_{ZT}	Z_{ZK} @ I_{ZK} = 0.5mA	I_R	@ V_R
Nom (V)	Min (V)	Max (V)	mA	Ω		µA	V
5.6	5.49	5.73	5	60	200	1.0	2.5

Note: 6. Short duration pulse test used to minimize self-heating effect.

NPN Transistor (Q1)

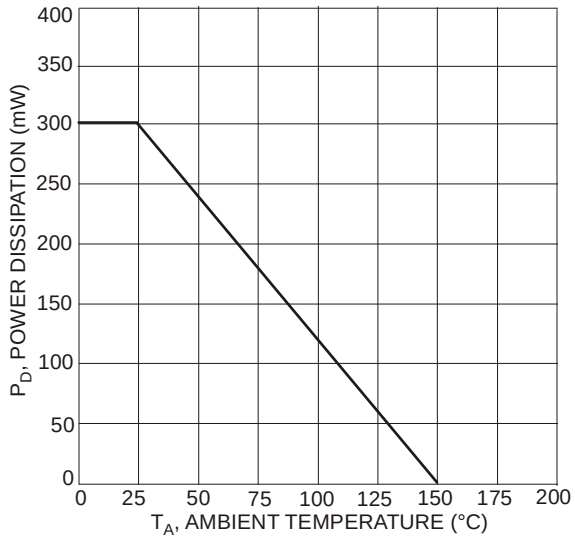


Fig. 1 Power Dissipation vs. Ambient Temperature (Total Device)

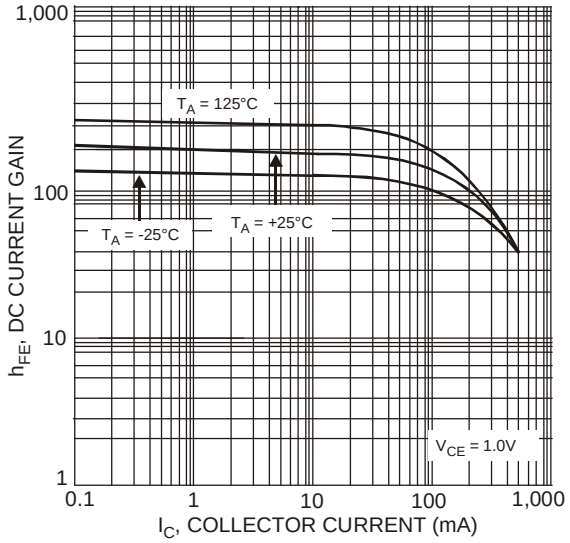


Fig. 2 Typical DC Current Gain vs. Collector Current

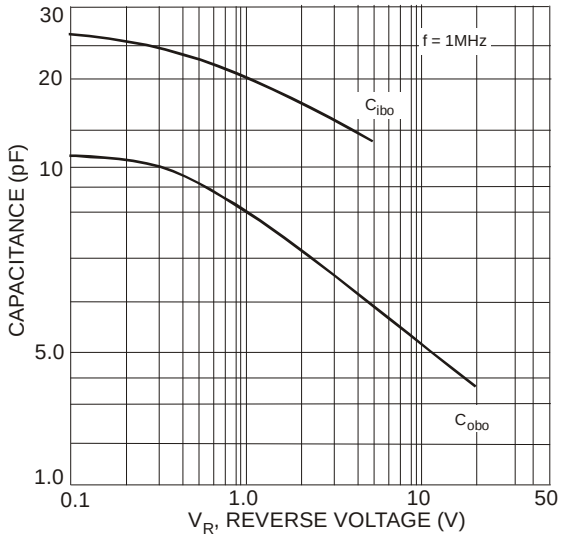


Fig. 3 Typical Capacitance Characteristics

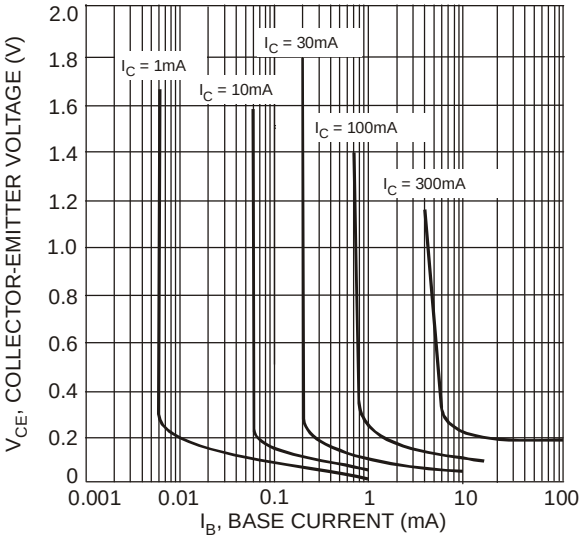


Fig. 4 Typical Collector Saturation Region

NPN Transistor (Q1) (Continued)

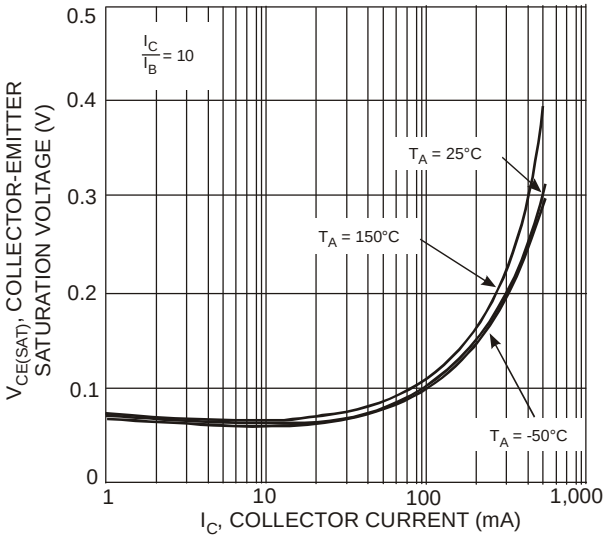


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

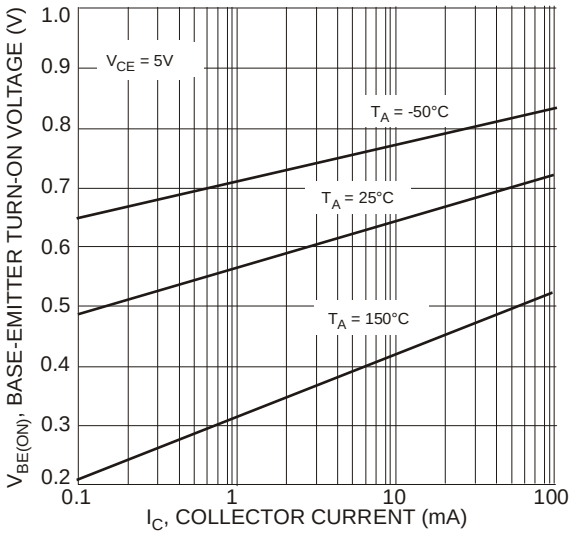


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

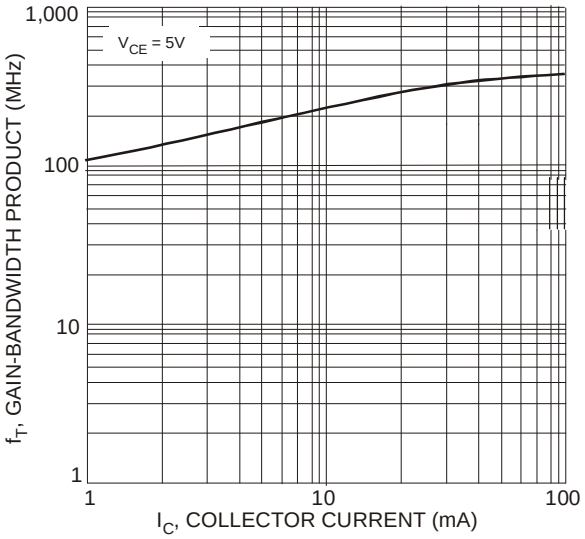


Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current

Zener (Z1)

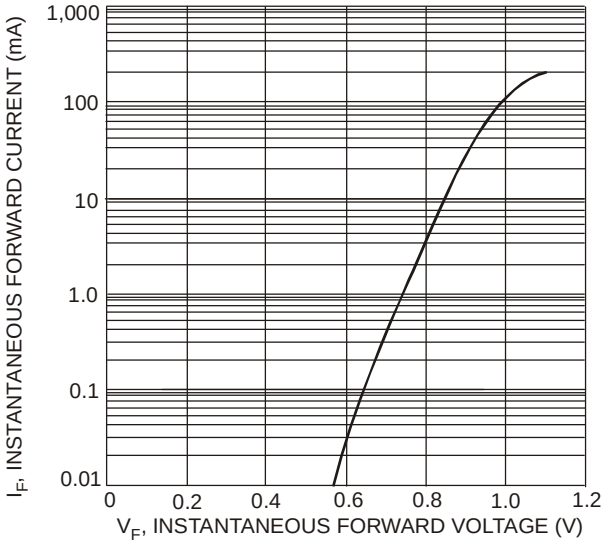
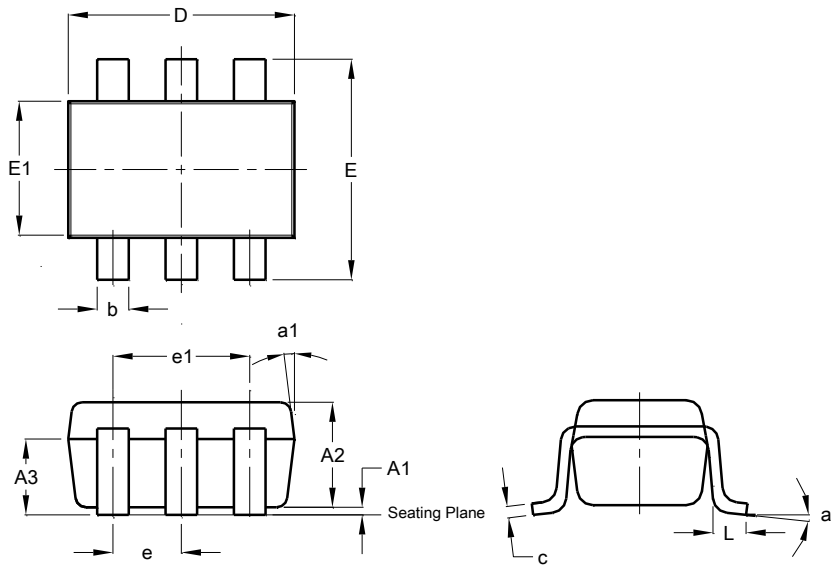


Fig. 8 Typical Forward Characteristics

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26 (SC74R)

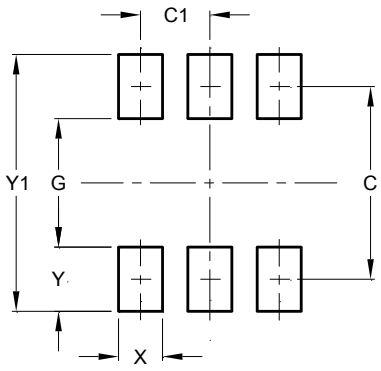


SOT26 (SC74R)			
Dim	**Min**	**Max**	**Typ**
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26 (SC74R)



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

www.diodes.com